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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I <sup>2</sup> C, LINbus, SPI, TSI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	70
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-FQFP (12x12)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl15z32vlk4">https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl15z32vlk4</a>

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## Terminology and guidelines

Field	Description	Values
R	Silicon revision	<ul style="list-style-type: none"><li>• (Blank) = Main</li><li>• A = Revision after main</li></ul>
T	Temperature range (°C)	<ul style="list-style-type: none"><li>• V = -40 to 105</li></ul>
PP	Package identifier	<ul style="list-style-type: none"><li>• FM = 32 QFN (5 mm x 5 mm)</li><li>• FT = 48 QFN (7 mm x 7 mm)</li><li>• LH = 64 LQFP (10 mm x 10 mm)</li><li>• LK = 80 LQFP (12 mm x 12 mm)</li></ul>
CC	Maximum CPU frequency (MHz)	<ul style="list-style-type: none"><li>• 4 = 48 MHz</li></ul>
N	Packaging type	<ul style="list-style-type: none"><li>• R = Tape and reel</li><li>• (Blank) = Trays</li></ul>

## 2.4 Example

This is an example part number:

MKL15Z32VFT4

## 3 Terminology and guidelines

### 3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

#### 3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V <sub>DD</sub>	1.0 V core supply voltage	0.9	1.1	V

### 3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

### 3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

#### 3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I <sub>WP</sub>	Digital I/O weak pullup/pulldown current	10	70	130	μA

#### 3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:

## 4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

## 4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
$V_{HBM}$	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
$V_{CDM}$	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
$I_{LAT}$	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

## 4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
$V_{DD}$	Digital supply voltage	-0.3	3.8	V
$I_{DD}$	Digital supply current	—	120	mA
$V_{DIO}$	Digital pin input voltage (except $\overline{RESET}$ )	-0.3	3.6	V
$V_{AIO}$	Analog pins <sup>1</sup> and $\overline{RESET}$ pin input voltage	-0.3	$V_{DD} + 0.3$	V
$I_D$	Instantaneous maximum current single pin limit (applies to all port pins)	-25	25	mA
$V_{DDA}$	Analog supply voltage	$V_{DD} - 0.3$	$V_{DD} + 0.3$	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

## 5 General

**Table 1. Voltage and current operating requirements (continued)**

Symbol	Description	Min.	Max.	Unit	Notes
$I_{CDIO}$	Digital pin negative DC injection current — single pin <ul style="list-style-type: none"> <li><math>V_{IN} &lt; V_{SS}-0.3V</math></li> </ul>	-5	—	mA	1
$I_{CAIO}$	Analog <sup>2</sup> pin DC injection current — single pin <ul style="list-style-type: none"> <li><math>V_{IN} &lt; V_{SS}-0.3V</math> (Negative current injection)</li> <li><math>V_{IN} &gt; V_{DD}+0.3V</math> (Positive current injection)</li> </ul>	-5 —	— +5	mA	3
$I_{Ccont}$	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins <ul style="list-style-type: none"> <li>Negative current injection</li> <li>Positive current injection</li> </ul>	-25 —	— +25	mA	
$V_{RAM}$	$V_{DD}$ voltage required to retain RAM	1.2	—	V	

- All digital I/O pins are internally clamped to  $V_{SS}$  through a ESD protection diode. There is no diode connection to  $V_{DD}$ . If  $V_{IN}$  greater than  $V_{DIO\_MIN}$  ( $=V_{SS}-0.3V$ ) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as  $R=(V_{DIO\_MIN}-V_{IN})/|I_{ICL}|$ .
- Analog pins are defined as pins that do not have an associated general purpose I/O port function.
- All analog pins are internally clamped to  $V_{SS}$  and  $V_{DD}$  through ESD protection diodes. If  $V_{IN}$  is greater than  $V_{AIO\_MIN}$  ( $=V_{SS}-0.3V$ ) and  $V_{IN}$  is less than  $V_{AIO\_MAX}$  ( $=V_{DD}+0.3V$ ) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as  $R=(V_{AIO\_MIN}-V_{IN})/|I_{ICL}|$ . The positive injection current limiting resistor is calculated as  $R=(V_{IN}-V_{AIO\_MAX})/|I_{ICL}|$ . Select the larger of these two calculated resistances.

## 5.2.2 LVD and POR operating requirements

**Table 2.  $V_{DD}$  supply LVD and POR operating requirements**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$V_{POR}$	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
$V_{LVDH}$	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
$V_{LVW1H}$	Low-voltage warning thresholds — high range <ul style="list-style-type: none"> <li>Level 1 falling (LVWV=00)</li> </ul>	2.62	2.70	2.78	V	1
$V_{LVW2H}$	<ul style="list-style-type: none"> <li>Level 2 falling (LVWV=01)</li> </ul>	2.72	2.80	2.88	V	
$V_{LVW3H}$	<ul style="list-style-type: none"> <li>Level 3 falling (LVWV=10)</li> </ul>	2.82	2.90	2.98	V	
$V_{LVW4H}$	<ul style="list-style-type: none"> <li>Level 4 falling (LVWV=11)</li> </ul>	2.92	3.00	3.08	V	
$V_{HYSH}$	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	
$V_{LVDL}$	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	

Table continues on the next page...

**Table 3. Voltage and current operating behaviors (continued)**

Symbol	Description	Min.	Max.	Unit	Notes
R <sub>PU</sub>	Internal pullup resistors	20	50	kΩ	3
R <sub>PD</sub>	Internal pulldown resistors	20	50	kΩ	4

1. PTB0, PTB1, PTD6, and PTD7 I/O have both high drive and normal drive capability selected by the associated PTx\_PCRn[DSE] control bit. All other GPIOs are normal drive only.
2. Measured at V<sub>DD</sub> = 3.6 V
3. Measured at V<sub>DD</sub> supply voltage = V<sub>DD</sub> min and V<sub>input</sub> = V<sub>SS</sub>
4. Measured at V<sub>DD</sub> supply voltage = V<sub>DD</sub> min and V<sub>input</sub> = V<sub>DD</sub>

## 5.2.4 Power mode transition operating behaviors

All specifications except t<sub>POR</sub> and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- FEI clock mode

**Table 4. Power mode transition operating behaviors**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t <sub>POR</sub>	After a POR event, amount of time from the point V <sub>DD</sub> reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	—	—	300	μs	
	• VLLS0 → RUN	—	95	115	μs	
	• VLLS1 → RUN	—	93	115	μs	
	• VLLS3 → RUN	—	42	53	μs	
	• LLS → RUN	—	4	4.6	μs	
	• VLPS → RUN	—	4	4.4	μs	
	• STOP → RUN	—	4	4.4	μs	

## 5.4.2 Thermal attributes

**Table 10. Thermal attributes**

Board type	Symbol	Description	80 LQFP	64 LQFP	48 QFN	32 QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	70	71	84	92	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	53	52	28	33	°C/W	
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	—	59	69	75	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	—	46	22	27	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	34	34	10	12	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	15	20	2.0	1.8	°C/W	3
—	$\Psi_{JT}$	Thermal characterization parameter, junction to package top outside center (natural convection)	0.6	5	5.0	8	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions – Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions – Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions – Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions – Natural Convection (Still Air)*.

## 6 Peripheral operating requirements and behaviors

### 6.1 Core modules

#### 6.1.1 SWD Electricals

**Table 11. SWD full voltage range electricals**

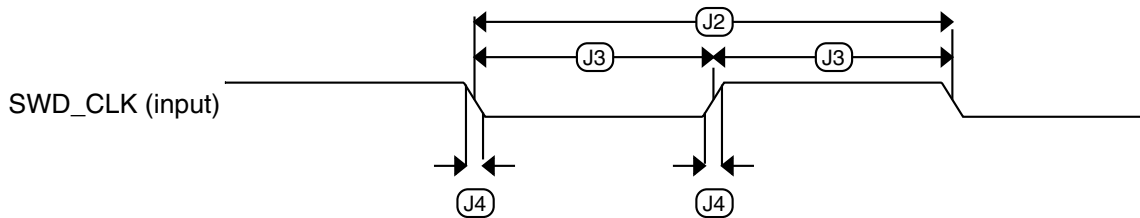
Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V

Table continues on the next page...

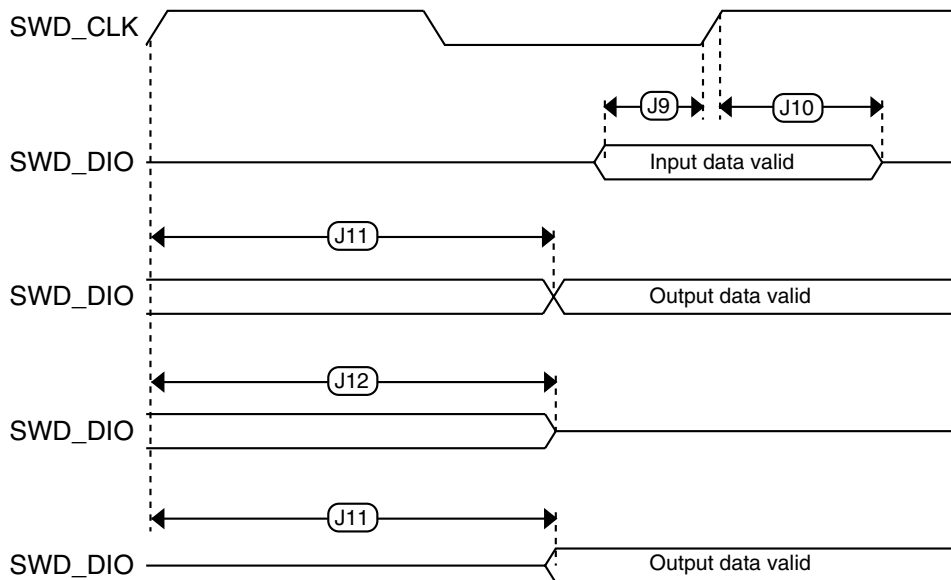


**Table 11. SWD full voltage range electricals (continued)**

Symbol	Description	Min.	Max.	Unit
J1	SWD_CLK frequency of operation <ul style="list-style-type: none"> <li>Serial wire debug</li> </ul>	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width <ul style="list-style-type: none"> <li>Serial wire debug</li> </ul>	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns



**Figure 4. Serial wire clock input timing**



**Figure 5. Serial wire data timing**

**Table 12. MCG specifications (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes	
$f_{\text{dco\_t\_DMX32}}$	DCO output frequency	Low range (DRS = 00) $732 \times f_{\text{fil\_ref}}$	—	23.99	—	MHz	5, 6
		Mid range (DRS = 01) $1464 \times f_{\text{fil\_ref}}$	—	47.97	—	MHz	
$J_{\text{cyc\_fll}}$	FLL period jitter • $f_{\text{VCO}} = 48$ MHz	—	180	—	ps	7	
$t_{\text{fll\_acquire}}$	FLL target frequency acquisition time	—	—	1	ms	8	
PLL							
$f_{\text{vco}}$	VCO operating frequency	48.0	—	100	MHz		
$I_{\text{pll}}$	PLL operating current • PLL at 96 MHz ( $f_{\text{osc\_hi\_1}} = 8$ MHz, $f_{\text{pll\_ref}} = 2$ MHz, VDIV multiplier = 48)	—	1060	—	$\mu\text{A}$	9	
$I_{\text{pll}}$	PLL operating current • PLL at 48 MHz ( $f_{\text{osc\_hi\_1}} = 8$ MHz, $f_{\text{pll\_ref}} = 2$ MHz, VDIV multiplier = 24)	—	600	—	$\mu\text{A}$	9	
$f_{\text{pll\_ref}}$	PLL reference frequency range	2.0	—	4.0	MHz		
$J_{\text{cyc\_pll}}$	PLL period jitter (RMS) • $f_{\text{vco}} = 48$ MHz • $f_{\text{vco}} = 100$ MHz	—	120	—	ps	10	
		—	50	—	ps		
$J_{\text{acc\_pll}}$	PLL accumulated jitter over 1 $\mu\text{s}$ (RMS) • $f_{\text{vco}} = 48$ MHz • $f_{\text{vco}} = 100$ MHz	—	1350	—	ps	10	
		—	600	—	ps		
$D_{\text{lock}}$	Lock entry frequency tolerance	$\pm 1.49$	—	$\pm 2.98$	%		
$D_{\text{unl}}$	Lock exit frequency tolerance	$\pm 4.47$	—	$\pm 5.97$	%		
$t_{\text{pll\_lock}}$	Lock detector detection time	—	—	$150 \times 10^{-6} + 1075(1/f_{\text{pll\_ref}})$	s	11	

- This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
- The deviation is relative to the factory trimmed frequency at nominal  $V_{\text{DD}}$  and 25 °C,  $f_{\text{ints\_ft}}$ .
- These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
- The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation ( $\Delta f_{\text{dco\_t}}$ ) over voltage and temperature must be considered.
- These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
- The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
- This specification is based on standard deviation (RMS) of period or frequency.
- This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- Excludes any oscillator currents that are also consuming power while PLL is in operation.
- This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
- This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

## 6.3.2 Oscillator electrical specifications

This section provides the electrical characteristics of the module.

### 6.3.2.1 Oscillator DC electrical specifications

Table 13. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$V_{DD}$	Supply voltage	1.71	—	3.6	V	
$I_{DDOSC}$	Supply current — low-power mode (HGO=0) <ul style="list-style-type: none"> <li>• 32 kHz</li> <li>• 4 MHz</li> <li>• 8 MHz (RANGE=01)</li> <li>• 16 MHz</li> <li>• 24 MHz</li> <li>• 32 MHz</li> </ul>	—	500	—	nA	1
		—	200	—	$\mu$ A	
		—	300	—	$\mu$ A	
		—	950	—	$\mu$ A	
		—	1.2	—	mA	
		—	1.5	—	mA	
$I_{DDOSC}$	Supply current — high gain mode (HGO=1) <ul style="list-style-type: none"> <li>• 32 kHz</li> <li>• 4 MHz</li> <li>• 8 MHz (RANGE=01)</li> <li>• 16 MHz</li> <li>• 24 MHz</li> <li>• 32 MHz</li> </ul>	—	25	—	$\mu$ A	1
		—	400	—	$\mu$ A	
		—	500	—	$\mu$ A	
		—	2.5	—	mA	
		—	3	—	mA	
		—	4	—	mA	
$C_x$	EXTAL load capacitance	—	—	—		2, 3
$C_y$	XTAL load capacitance	—	—	—		2, 3
$R_F$	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	M $\Omega$	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	M $\Omega$	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	M $\Omega$	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	M $\Omega$	

Table continues on the next page...

### 6.4.1.2 Flash timing specifications — commands

**Table 16. Flash command timing specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	$\mu$ s	1
$t_{pgmchk}$	Program Check execution time	—	—	45	$\mu$ s	1
$t_{rdsrc}$	Read Resource execution time	—	—	30	$\mu$ s	1
$t_{pgm4}$	Program Longword execution time	—	65	145	$\mu$ s	
$t_{ersscr}$	Erase Flash Sector execution time	—	14	114	ms	2
$t_{rd1all}$	Read 1s All Blocks execution time	—	—	1.8	ms	
$t_{rdonce}$	Read Once execution time	—	—	25	$\mu$ s	1
$t_{pgmonce}$	Program Once execution time	—	65	—	$\mu$ s	
$t_{ersall}$	Erase All Blocks execution time	—	62	500	ms	2
$t_{vfykey}$	Verify Backdoor Access Key execution time	—	—	30	$\mu$ s	1

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

### 6.4.1.3 Flash high voltage current behaviors

**Table 17. Flash high voltage current behaviors**

Symbol	Description	Min.	Typ.	Max.	Unit
$I_{DD\_PGM}$	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
$I_{DD\_ERS}$	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

### 6.4.1.4 Reliability specifications

**Table 18. NVM reliability specifications**

Symbol	Description	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at  $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$ .

## 6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

## 6.6 Analog

### 6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in [Table 19](#) and [Table 20](#) are achievable on the differential pins ADCx\_DP0, ADCx\_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

#### 6.6.1.1 16-bit ADC operating conditions

**Table 19. 16-bit ADC operating conditions**

Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
V <sub>DDA</sub>	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV <sub>DDA</sub>	Supply voltage	Delta to V <sub>DD</sub> (V <sub>DD</sub> -V <sub>DDA</sub> )	-100	0	+100	mV	2
ΔV <sub>SSA</sub>	Ground voltage	Delta to V <sub>SS</sub> (V <sub>SS</sub> - V <sub>SSA</sub> )	-100	0	+100	mV	2
V <sub>REFH</sub>	ADC reference voltage high		1.13	V <sub>DDA</sub>	V <sub>DDA</sub>	V	3
V <sub>REFL</sub>	ADC reference voltage low		V <sub>SSA</sub>	V <sub>SSA</sub>	V <sub>SSA</sub>	V	3
V <sub>ADIN</sub>	Input voltage		V <sub>REFL</sub>	—	V <sub>REFH</sub>	V	
C <sub>ADIN</sub>	Input capacitance	<ul style="list-style-type: none"> <li>16-bit mode</li> <li>8-/10-/12-bit modes</li> </ul>	—	8	10	pF	
R <sub>ADIN</sub>	Input resistance		—	2	5	kΩ	
R <sub>AS</sub>	Analog source resistance	13-/12-bit modes f <sub>ADCK</sub> < 4 MHz	—	—	5	kΩ	4
f <sub>ADCK</sub>	ADC conversion clock frequency	≤ 13/12-bit mode	1.0	—	18.0	MHz	5
f <sub>ADCK</sub>	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	5
C <sub>rate</sub>	ADC conversion rate	≤ 13/12 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	6

Table continues on the next page...

**Table 20. 16-bit ADC characteristics ( $V_{REFH} = V_{DDA}$ ,  $V_{REFL} = V_{SSA}$ ) (continued)**

Symbol	Description	Conditions <sup>1</sup>	Min.	Typ. <sup>2</sup>	Max.	Unit	Notes
$f_{ADACK}$	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	$t_{ADACK} = 1/f_{ADACK}$
		• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	
		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz	
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz	
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	$\pm 4$ $\pm 1.4$	$\pm 6.8$ $\pm 2.1$	LSB <sup>4</sup>	5
DNL	Differential non-linearity	• 12-bit modes  • <12-bit modes	— —	$\pm 0.7$ $\pm 0.2$	-1.1 to +1.9 -0.3 to 0.5	LSB <sup>4</sup>	5
INL	Integral non-linearity	• 12-bit modes  • <12-bit modes	— —	$\pm 1.0$ $\pm 0.5$	-2.7 to +1.9 -0.7 to +0.5	LSB <sup>4</sup>	5
$E_{FS}$	Full-scale error	• 12-bit modes • <12-bit modes	— —	-4 -1.4	-5.4 -1.8	LSB <sup>4</sup>	$V_{ADIN} = V_{DDA}$ 5
$E_Q$	Quantization error	• 16-bit modes • $\leq 1312$ -bit modes	— —	-1 to 0 —	— $\pm 0.5$	LSB <sup>4</sup>	
ENOB	Effective number of bits	16-bit differential mode					6
		• Avg = 32	12.8	14.5	—	bits	
		• Avg = 4	11.9	13.8	—	bits	
		16-bit single-ended mode					
• Avg = 32	12.2	13.9	—	bits			
• Avg = 4	11.4	13.1	—	bits			
SINAD	Signal-to-noise plus distortion	See ENOB	$6.02 \times \text{ENOB} + 1.76$			dB	
THD	Total harmonic distortion	16-bit differential mode					7
		• Avg = 32	—	-94	—	dB	
		16-bit single-ended mode					
		• Avg = 32	—	-85	—	dB	
SFDR	Spurious free dynamic range	16-bit differential mode					7
		• Avg = 32	82	95	—	dB	
		16-bit single-ended mode					
		• Avg = 32	78	90	—	dB	

Table continues on the next page...

Typical ADC 16-bit Single-Ended ENOB vs ADC Clock  
100Hz, 90% FS Sine Input

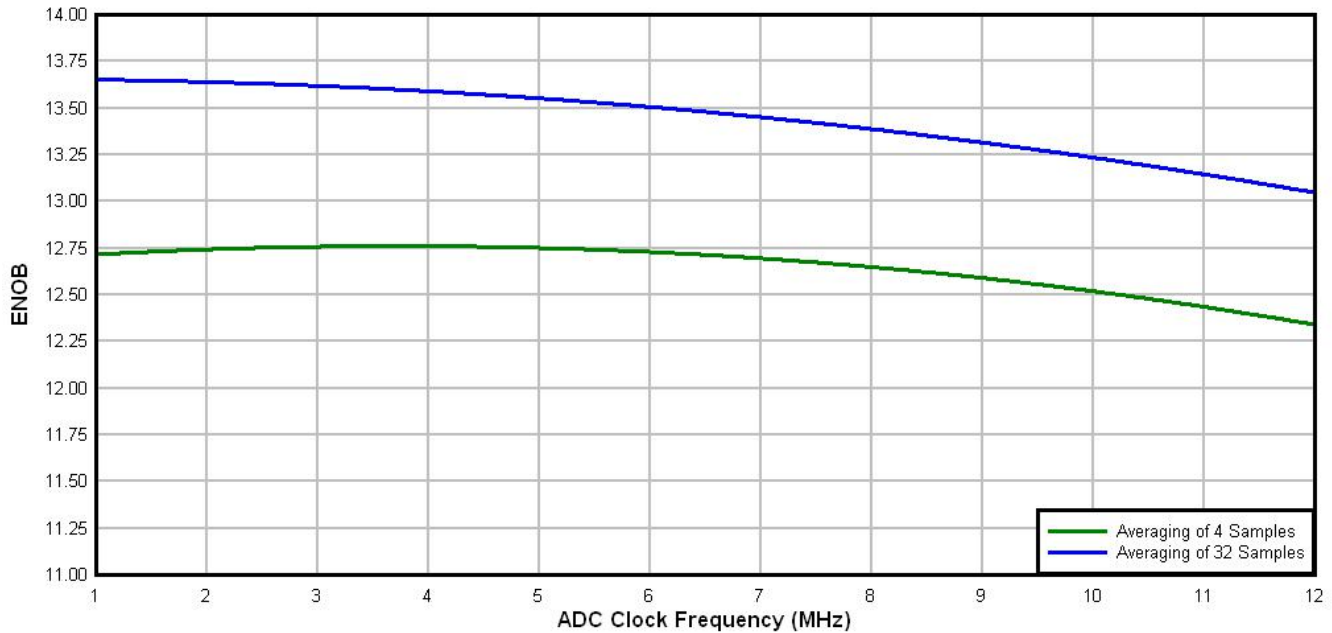


Figure 8. Typical ENOB vs. ADC\_CLK for 16-bit single-ended mode

## 6.6.2 CMP and 6-bit DAC electrical specifications

Table 21. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
$V_{DD}$	Supply voltage	1.71	—	3.6	V
$I_{DDHS}$	Supply current, high-speed mode (EN = 1, PMODE = 1)	—	—	200	$\mu$ A
$I_{DDL S}$	Supply current, low-speed mode (EN = 1, PMODE = 0)	—	—	20	$\mu$ A
$V_{AIN}$	Analog input voltage	$V_{SS}$	—	$V_{DD}$	V
$V_{AIO}$	Analog input offset voltage	—	—	20	mV
$V_H$	Analog comparator hysteresis <sup>1</sup> <ul style="list-style-type: none"> <li>• CR0[HYSTCTR] = 00</li> <li>• CR0[HYSTCTR] = 01</li> <li>• CR0[HYSTCTR] = 10</li> <li>• CR0[HYSTCTR] = 11</li> </ul>	—	5 10 20 30	—	mV
$V_{CMPOH}$	Output high	$V_{DD} - 0.5$	—	—	V
$V_{CMPOI}$	Output low	—	—	0.5	V
$t_{DHS}$	Propagation delay, high-speed mode (EN = 1, PMODE = 1)	20	50	200	ns
$t_{DLS}$	Propagation delay, low-speed mode (EN = 1, PMODE = 0)	80	250	600	ns

Table continues on the next page...

### 6.6.3.1 12-bit DAC operating requirements

Table 22. 12-bit DAC operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
$V_{DDA}$	Supply voltage	1.71	3.6	V	
$V_{DACR}$	Reference voltage	1.13	3.6	V	1
$T_A$	Temperature	Operating temperature range of the device		°C	
$C_L$	Output load capacitance	—	100	pF	2
$I_L$	Output load current	—	1	mA	

1. The DAC reference can be selected to be  $V_{DDA}$  or the voltage output of the VREF module (VREF\_OUT)
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC

### 6.6.3.2 12-bit DAC operating behaviors

Table 23. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$I_{DDA\_DACLP}$	Supply current — low-power mode	—	—	250	μA	
$I_{DDA\_DACHP}$	Supply current — high-speed mode	—	—	900	μA	
$t_{DACLP}$	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
$t_{DACHP}$	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	$V_{DACR} - 100$	—	$V_{DACR}$	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2$ V	—	—	±1	LSB	3
DNL	Differential non-linearity error — $V_{DACR} = VREF\_OUT$	—	—	±1	LSB	4
$V_{OFFSET}$	Offset error	—	±0.4	±0.8	%FSR	5
$E_G$	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4$ V	60	—	90	dB	
$T_{CO}$	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
$T_{GE}$	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
R <sub>op</sub>	Output resistance load = 3 kΩ	—	—	250	Ω	

Table continues on the next page...



## Peripheral operating requirements and behaviors

All timing is shown with respect to 20%  $V_{DD}$  and 80%  $V_{DD}$  thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

**Table 24. SPI master mode timing on slew rate disabled pads**

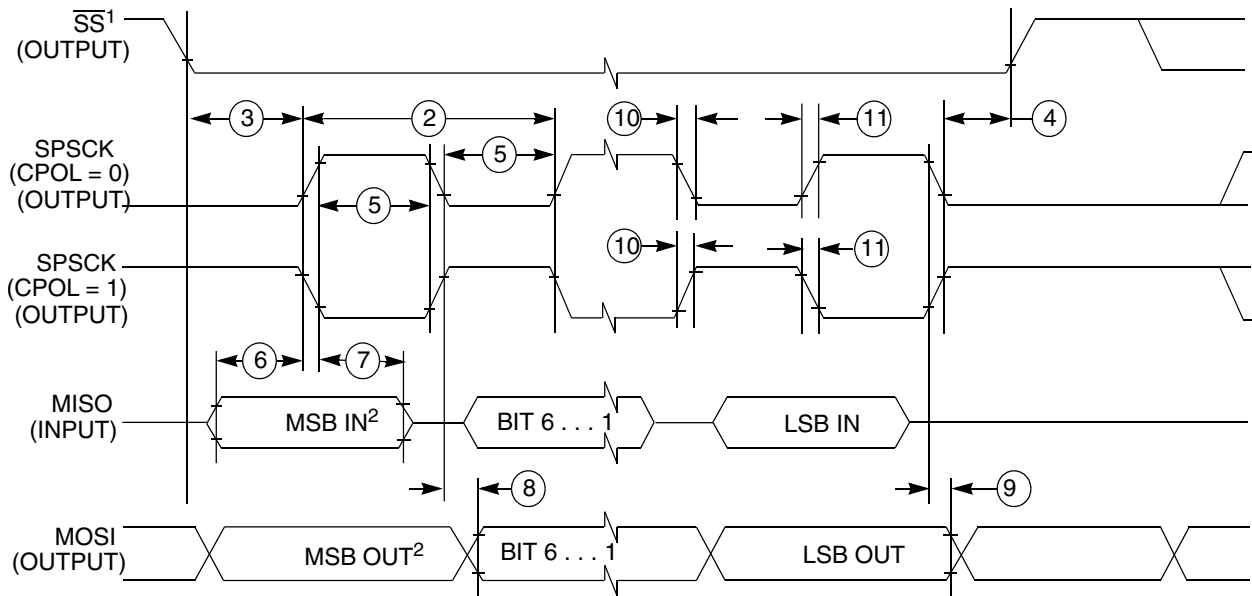
Num.	Symbol	Description	Min.	Max.	Unit	Note
1	$f_{op}$	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	$t_{SPSCK}$	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	$t_{Lead}$	Enable lead time	1/2	—	$t_{SPSCK}$	—
4	$t_{Lag}$	Enable lag time	1/2	—	$t_{SPSCK}$	—
5	$t_{WSPSCK}$	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	$t_{SU}$	Data setup time (inputs)	16	—	ns	—
7	$t_{HI}$	Data hold time (inputs)	0	—	ns	—
8	$t_v$	Data valid (after SPSCK edge)	—	10	ns	—
9	$t_{HO}$	Data hold time (outputs)	0	—	ns	—
10	$t_{RI}$	Rise time input	—	$t_{periph} - 25$	ns	—
	$t_{FI}$	Fall time input				
11	$t_{RO}$	Rise time output	—	25	ns	—
	$t_{FO}$	Fall time output				

1. For SPI0  $f_{periph}$  is the bus clock ( $f_{BUS}$ ). For SPI1  $f_{periph}$  is the system clock ( $f_{SYS}$ ).
2.  $t_{periph} = 1/f_{periph}$

**Table 25. SPI master mode timing on slew rate enabled pads**

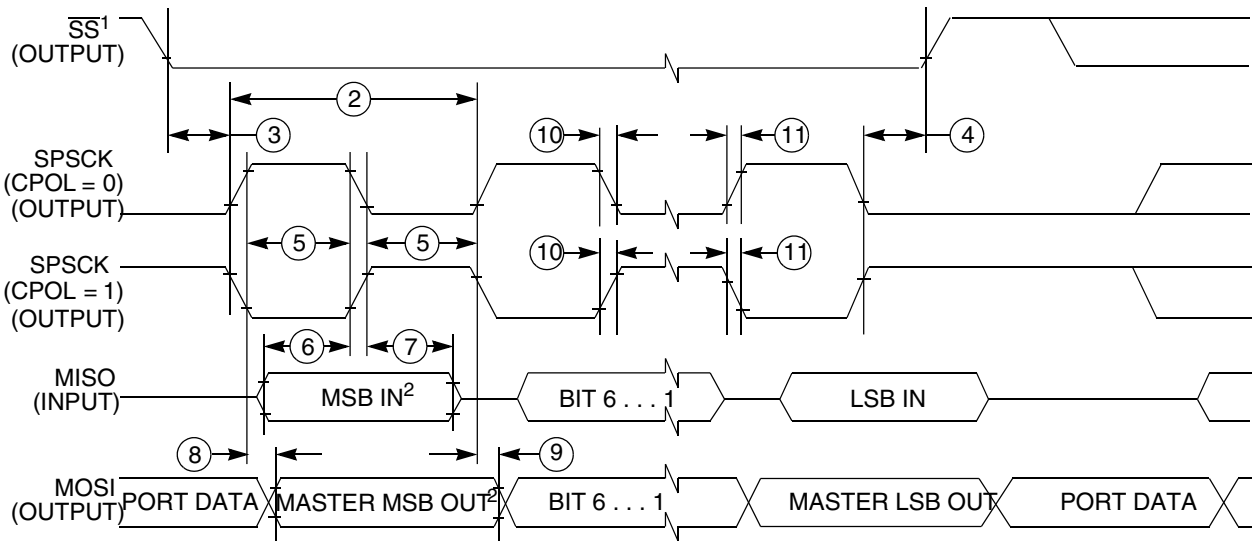
Num.	Symbol	Description	Min.	Max.	Unit	Note
1	$f_{op}$	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	$t_{SPSCK}$	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	$t_{Lead}$	Enable lead time	1/2	—	$t_{SPSCK}$	—
4	$t_{Lag}$	Enable lag time	1/2	—	$t_{SPSCK}$	—
5	$t_{WSPSCK}$	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	$t_{SU}$	Data setup time (inputs)	96	—	ns	—
7	$t_{HI}$	Data hold time (inputs)	0	—	ns	—
8	$t_v$	Data valid (after SPSCK edge)	—	52	ns	—
9	$t_{HO}$	Data hold time (outputs)	0	—	ns	—
10	$t_{RI}$	Rise time input	—	$t_{periph} - 25$	ns	—
	$t_{FI}$	Fall time input				
11	$t_{RO}$	Rise time output	—	36	ns	—
	$t_{FO}$	Fall time output				

1. For SPI0  $f_{periph}$  is the bus clock ( $f_{BUS}$ ). For SPI1  $f_{periph}$  is the system clock ( $f_{SYS}$ ).
2.  $t_{periph} = 1/f_{periph}$



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

**Figure 13. SPI master mode timing (CPHA = 0)**



1. If configured as output
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

**Figure 14. SPI master mode timing (CPHA = 1)**

**Table 26. SPI slave mode timing on slew rate disabled pads**

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	$f_{op}$	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	$t_{SPSCCK}$	SPSCCK period	$4 \times t_{periph}$	—	ns	2
3	$t_{Lead}$	Enable lead time	1	—	$t_{periph}$	—
4	$t_{Lag}$	Enable lag time	1	—	$t_{periph}$	—
5	$t_{WSPSCCK}$	Clock (SPSCCK) high or low time	$t_{periph} - 30$	—	ns	—

Table continues on the next page...

## 6.9 Human-machine interfaces (HMI)

### 6.9.1 TSI electrical specifications

**Table 28. TSI electrical specifications**

Symbol	Description	Min.	Type	Max	Unit
TSI_RUNF	Fixed power consumption in run mode	—	100	—	μA
TSI_RUNV	Variable power consumption in run mode (depends on oscillator's current selection)	1.0	—	128	μA
TSI_EN	Power consumption in enable mode	—	100	—	μA
TSI_DIS	Power consumption in disable mode	—	1.2	—	μA
TSI_TEN	TSI analog enable time	—	66	—	μs
TSI_CREF	TSI reference capacitor	—	1.0	—	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	0.19	—	1.03	V

## 7 Dimensions

### 7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to [www.freescale.com](http://www.freescale.com) and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin QFN	98ASA00473D
48-pin QFN	98ASA00466D
64-pin LQFP	98ASS23234W
80-pin LQFP	98ASS23174W

## 8 Pinout

## 8.1 KL15 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	1	—	1	PTE0	DISABLED		PTE0		UART1_TX	RTC_CLKOUT	CMPO_OUT	I2C1_SDA	
2	2	—	2	PTE1	DISABLED		PTE1	SPI1_MOSI	UART1_RX		SPI1_MISO	I2C1_SCL	
3	—	—	—	PTE2	DISABLED		PTE2	SPI1_SCK					
4	—	—	—	PTE3	DISABLED		PTE3	SPI1_MISO			SPI1_MOSI		
5	—	—	—	PTE4	DISABLED		PTE4	SPI1_PCS0					
6	—	—	—	PTE5	DISABLED		PTE5						
7	3	1	—	VDD	VDD	VDD							
8	4	2	—	VSS	VSS	VSS							
9	5	3	3	PTE16	ADC0_DP1/ ADC0_SE1	ADC0_DP1/ ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_CLKIN0			
10	6	4	4	PTE17	ADC0_DM1/ ADC0_SE5a	ADC0_DM1/ ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_CLKIN1		LPTMR0_ ALT3	
11	7	5	5	PTE18	ADC0_DP2/ ADC0_SE2	ADC0_DP2/ ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO		
12	8	6	6	PTE19	ADC0_DM2/ ADC0_SE6a	ADC0_DM2/ ADC0_SE6a	PTE19	SPI0_MISO		I2C0_SCL	SPI0_MOSI		
13	9	7	—	PTE20	ADC0_DP0/ ADC0_SE0	ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	UART0_TX			
14	10	8	—	PTE21	ADC0_DM0/ ADC0_SE4a	ADC0_DM0/ ADC0_SE4a	PTE21		TPM1_CH1	UART0_RX			
15	11	—	—	PTE22	ADC0_DP3/ ADC0_SE3	ADC0_DP3/ ADC0_SE3	PTE22		TPM2_CH0	UART2_TX			
16	12	—	—	PTE23	ADC0_DM3/ ADC0_SE7a	ADC0_DM3/ ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX			
17	13	9	7	VDDA	VDDA	VDDA							
18	14	10	—	VREFH	VREFH	VREFH							
19	15	11	—	VREFL	VREFL	VREFL							
20	16	12	8	VSSA	VSSA	VSSA							
21	17	13	—	PTE29	CMPO_IN5/ ADC0_SE4b	CMPO_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_CLKIN0			
22	18	14	9	PTE30	DAC0_OUT/ ADC0_SE23/ CMPO_IN4	DAC0_OUT/ ADC0_SE23/ CMPO_IN4	PTE30		TPM0_CH3	TPM_CLKIN1			
23	19	—	—	PTE31	DISABLED		PTE31		TPM0_CH4				
24	20	15	—	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
25	21	16	—	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
26	22	17	10	PTA0	SWD_CLK	TSIO_CH1	PTA0		TPM0_CH5				SWD_CLK
27	23	18	11	PTA1	DISABLED	TSIO_CH2	PTA1	UART0_RX	TPM2_CH0				
28	24	19	12	PTA2	DISABLED	TSIO_CH3	PTA2	UART0_TX	TPM2_CH1				

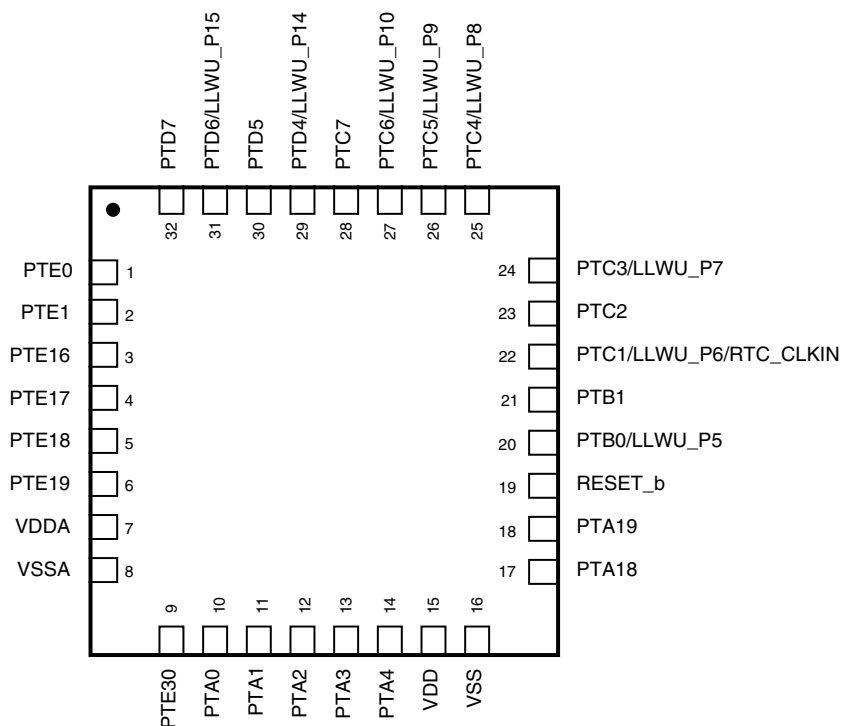


Figure 20. KL15 32-pin QFN pinout diagram

## 9 Revision History

The following table provides a revision history for this document.

**Table 29. Revision History**

Rev. No.	Date	Substantial Changes
1	7/2012	Initial NDA release.
2	9/2012	Completed all the TBDs, initial public release.
3	9/2012	Updated Signal Multiplexing and Pin Assignments table to add UART2 signals.